

In the Claims:

The status of the pending claims is as follows:

1. (Original) A thin film transistor comprising:

a current path pattern defining a current path, said current path pattern being made of semiconductor material and formed on a substrate;

a gate pattern crossing said current path pattern at least in first and second cross areas, said gate pattern defining a channel region of said current path pattern in an area superposed upon by said gate pattern; and

a gate insulating film disposed between said current path pattern and said gate pattern in the first and second cross areas,

wherein said current path pattern has an LDD structure on both sides of the channel region in the first cross area, the LDD structure including low concentration regions in contact with the channel region and high concentration regions in contact with the low concentration regions, and has an impurity concentration in areas in contact with the channel region in the second cross area higher than an impurity concentration of the low impurity concentration regions.

2. (Original) A liquid crystal display substrate comprising:

a plurality of gate bus lines extending in a row direction and formed on a substrate;

a plurality of drain bus lines extending in a column direction and formed on the substrate, said drain bus lines being electrically insulated from said gate bus lines in cross areas in which said gate bus lines cross with said drain bus lines;

pixel electrodes disposed in cross areas between said gate bus lines and said drain bus lines;

current path patterns corresponding to cross points between said gate bus lines and said drain bus lines, said current path patterns being made of semiconductor material and crossing a corresponding gate bus line at least at two points, channel regions of said current path patterns being formed in areas superposed upon by said gate bus lines, a first end portion of each said current path pattern being electrically connected to a corresponding drain bus line, and a second end portion of each said current path pattern being electrically connected to a corresponding pixel electrode; and

gate insulating films disposed between said gate bus lines and said current path patterns in the cross area,

wherein each said current path pattern has an LDD structure on both sides of the channel region nearer to the first end portion, the LDD structure including low concentration regions in contact with the channel region and high concentration regions in contact with the low concentration regions, and has an impurity concentration in areas in contact with the channel region nearer to the second end portion higher than an impurity concentration of the low impurity concentration regions.

3. (Original) A method of manufacturing a semiconductor display substrate, comprising the steps of:

preparing a substrate in which an image display area and a peripheral circuit area are defined, the peripheral circuit area being disposed at a side of the image display area;

forming a plurality of first current path patterns distributed in a matrix shape on the substrate in the image display area and a second current path pattern in the peripheral circuit area, in such a manner that each of the first current path patterns includes a portion flowing current at least in a column direction and the second current path pattern includes a portion flowing current at least in a row direction;

covering the first and second current path patterns with a gate insulating film;

forming a plurality of gate patterns on the gate insulating film in such a manner that the gate pattern crosses the column directionally flowing current portion of the first current path pattern in the image display area and crosses the row directionally flowing current portion of the second current path pattern in the peripheral circuit area;

implanting impurity ions into the first and second current path patterns by using the gate patterns as masks; and

irradiating an energy beam into the first and second current path patterns along an oblique direction relative to the substrate surface to activate doped impurities so that

the energy beam is irradiated in the first current path patterns in a shaded state of one of both sides of the gate patterns and irradiated in the second current pattern on both sides of the gate pattern.

4-9. (Cancelled)